Transmissive Sensor

FEATURES

- Phototransistor output
- · Accurate position sensing
- · Choice of detector aperture
- 0.125 in.(3.18 mm) slot width
- Dust protective housing



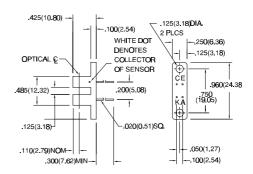
DESCRIPTION

The HOA1879 series consists of an infrared emitting diode facing an NPN silicon phototransistor encased in a black IR transmissive thermoplastic housing. Detector switching takes place whenever an opaque object passes through the slot between emitter and detector. The HOA1879 series employs an IR transmissive housing which features smooth optical faces without external aperture openings; this feature is desirable when aperture blockage from airborne contaminants is a possibility. The HOA1879-011 and -012 have a 0.060 in.(1.52 mm) dia. detector aperture, while the HOA1879-015 has a 0.010 in.(.25 mm) x 0.040 in. (1.02 mm) vertical aperture in front of the detector. This feature is ideal for use in applications where maximum position resolution is desired. The HOA1879 series employs plastic molded components. For additional component information see SEP8506 and SDP8406.

Housing material is IR transmissive polysulfone. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.010(0.25) 2 plc decimals ±0.020(0.51)



DIM_051.cdr



Transmissive Sensor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

DADAMETED	CVMDOL	BAINI	TVD	BAAV	LINUTO	TECT COMPITIONS
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IR EMITTER						
Forward Voltage	VF			1.6	V	I _F =20 mA
Reverse Leakage Current	I _R			10	μΑ	V _R =3 V
DETECTOR						
Collector-Emitter Breakdown Voltage	V _(BR) CEO	30			V	Ic=100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector Dark Current	Iceo			100	nA	V _{CE} =10 V, I _F =0
COUPLED CHARACTERISTICS						
On-State Collector Current	Ic(on)				mA	V _{CE} =5 V
HOA1879-011		0.4				I _F =20 mA
HOA1879-012		1.8				
HOA1879-015		0.5				
Collector-Emitter Saturation Voltage	VCE(SAT)				V	l _F =20 mA
HOA1879-011				0.4		lc=50 μA
HOA1879-012				0.4		Ic=220 μA
HOA1879-015				0.4		lc=60 μA
Rise And Fall Time	t _r , t _f				μs	Vcc=5 V, lc=1 mA
HOA1879-011, -012, -015			15		•	$R_L=1000 \Omega$

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Operating Temperature Range -40°C to 85°C
Storage Temperature Range -40°C to 85°C
Soldering Temperature (5 sec) 240°C

IR EMITTER

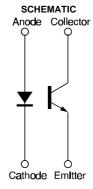
Power Dissipation 100 mW (1)
Reverse Voltage 3 V
Continuous Forward Current 50 mA

DETECTOR

Collector-Emitter Voltage 30 V
Emitter-Collector Voltage 5 V
Power Dissipation 100 mW (1)

Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

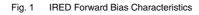
Collector DC Current

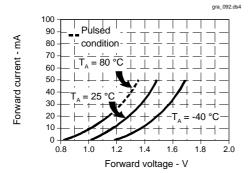




30 mA

Transmissive Sensor





100

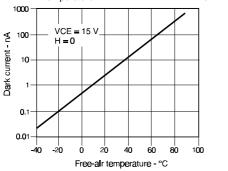
1000

Load resistance - Ohms

10000

10

Fig. 3 Dark Current vs Temperature



Collector Current vs Fig. 4 Ambient Temperature gra_095.ds4 Normalized collector current 1.0 0.6 0.4 0.2 0.0 75 -50 Ó 25 50 100 Free-air temperature - °C

All Performance Curves Show Typical Values

Transmissive Sensor



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